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Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if Known		
			Application Number	10/729,092	
			Filing Date	December 5, 2003	
			First Named Inventor	Lin, et al.	
			Art Unit	2811	
			Examiner Name	TBD	
Sheet	1	of	5	Attorney Docket Number	TSM03-0670

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
MEW	1	US-4,314,269	02-02-1982	Fujiki	
	2	US-4,631,803	12-30-1986	Hunter, et al.	
	3	US-4,946,799	08-07-1990	Blake, et al.	
	4	US-5,447,884	09-05-1995	Fahey, et al.	
	5	US-5,461,250	10-24-1995	Burghartz, et al.	
	6	US-5,534,713	07-09-1996	Ismail, et al.	
	7	US-5,629,544	05-13-1997	Voldman, et al.	
	8	US-5,714,777	02-03-1998	Ismail, et al.	
	9	US-5,763,315	06-09-1998	Benedict, et al.	
	10	US-5,811,857	09-22-1998	Assaderaght, et al.	
	11	US-6,008,095	12-28-1999	Gardner, et al.	
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	20	US-6,358,791 B1	03-19-2002	Hsu, et al.	
	21	US-6,387,739 B1	05-14-2002	Smith, III	
	22	US-2002/0076899 A1	06-20-2002	Skotnicki, et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ³
		Country Code ² - Number ⁴ - Kind Code ⁵ (if known)				
Mew	23	WO 03/017336 A2	02-27-2003	Amberwave Systems Corporation		

Examiner Signature	<i>Matthew EW</i>	Date Considered	12/22/04
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		Group Art Unit	2811
		Examiner Name	TBD
		Attorney Docket Number	TSM03-0670
Sheet	3	of	5

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cita. No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
grew	40	ISMAIL, K., <i>et al.</i> , "Electron Transport Properties of Si/SiGe Heterostructures: Measurements and Device Implications," Applied Physics Letters, Vol. 63, No. 5, (August 2, 1993), pp. 660-662.	
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Examiner Signature	Matthew E. N.		Date Considered 12/22/04

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		First Named Inventor	Lin, <i>et al.</i>		
		Group Art Unit	2811		
		Examiner Name	TBD		
Sheet	4	of	5	Attorney Docket Number	TSM03-0670

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
<i>Mew</i>	53	MATTHEWS, J.W., <i>et al.</i> , "Defects in Epitaxial Multilayers – III. Preparation of Almost Perfect Multilayers," Journal of Crystal Growth, Vol. 32, (1976), pp. 265-273.	
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Examiner Signature	<i>Matthew E. Wew</i>		Date Considered
			<i>12/22/04</i>

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				First Named Inventor	Lin, <i>et al.</i>
				Group Art Unit	2811
				Examiner Name	TBD
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MEW	66	CAVASSILAS, N., <i>et al.</i> , "Capacitance-Voltage Characteristics of Metal-Oxide-Strained Semiconductor Si/SiGe Heterostructures," Nanotech 2002, Vol. 1, pp. 600-603.	
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Examiner Signature	<i>Matthew E. Warner</i>	Date Considered	12/22/04
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Sheet

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Signature

Matthew E. Wam

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NON PATENT LITERATURE DOCUMENTS			
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mgw	13	LEITZ, C.W., et al., "Channel Engineering of SiGe-Based Heterostructures for High Mobility MOSFETs," Materials Research Society Symposium Proceedings, vol. 686, (2002), pp. 113-118.	
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Examiner Signature	<i>Matthew E. Warner</i>	Date Considered	1/3/04
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